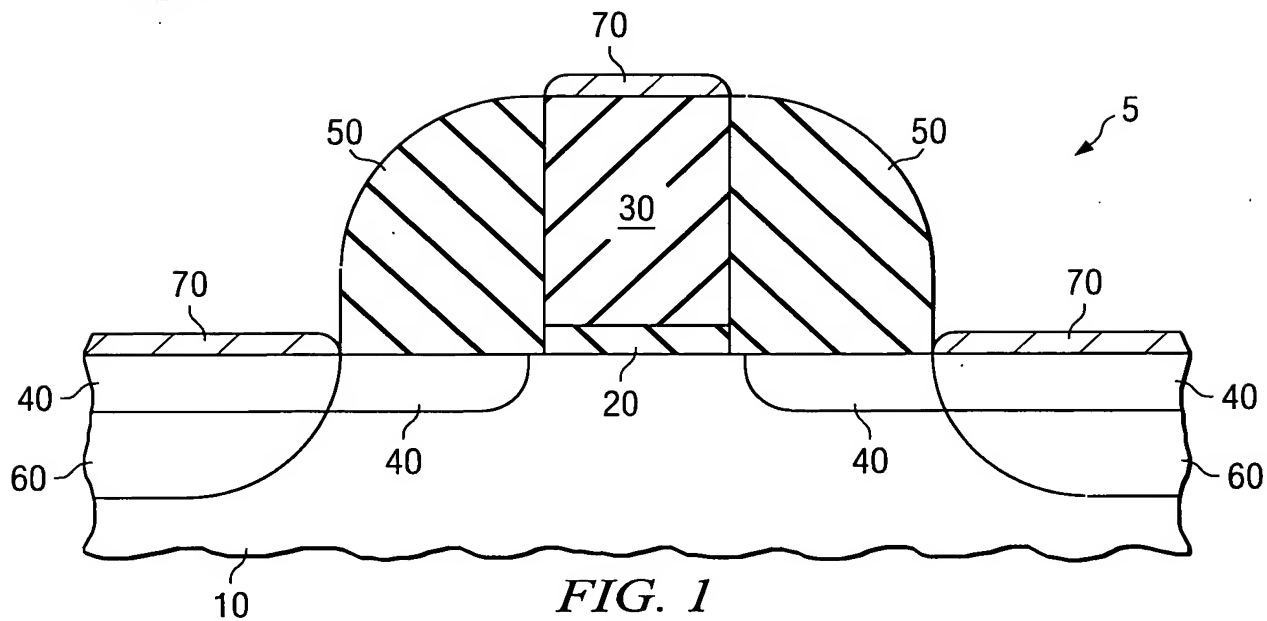
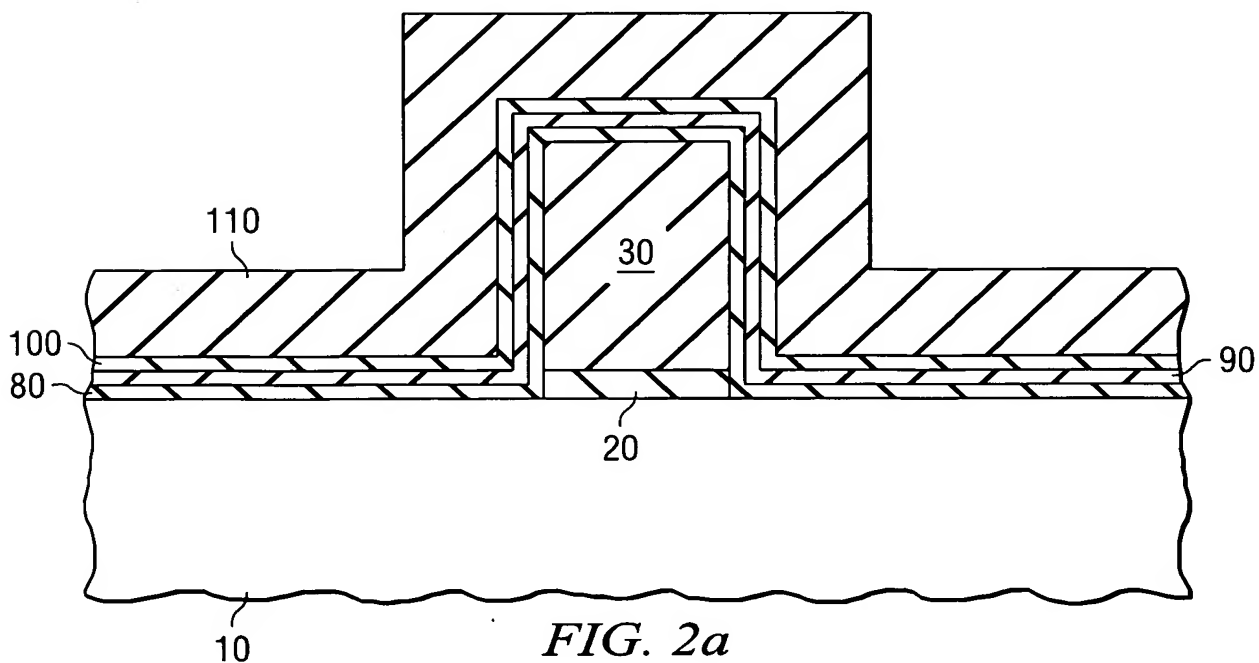




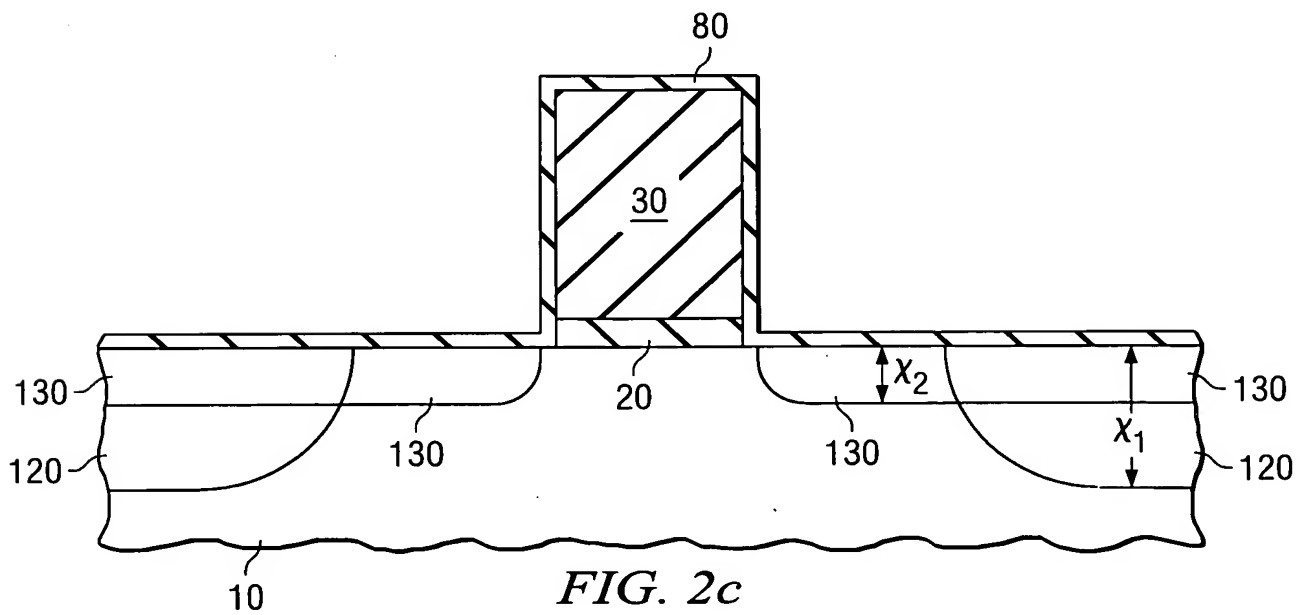
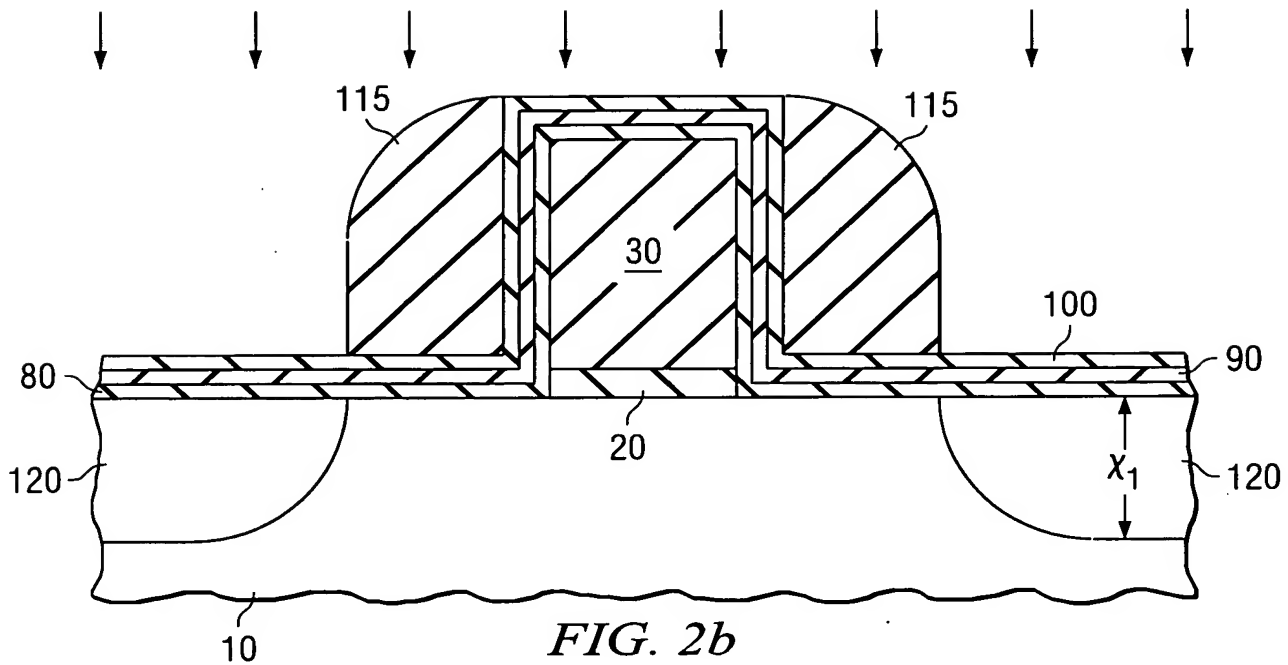
1/5



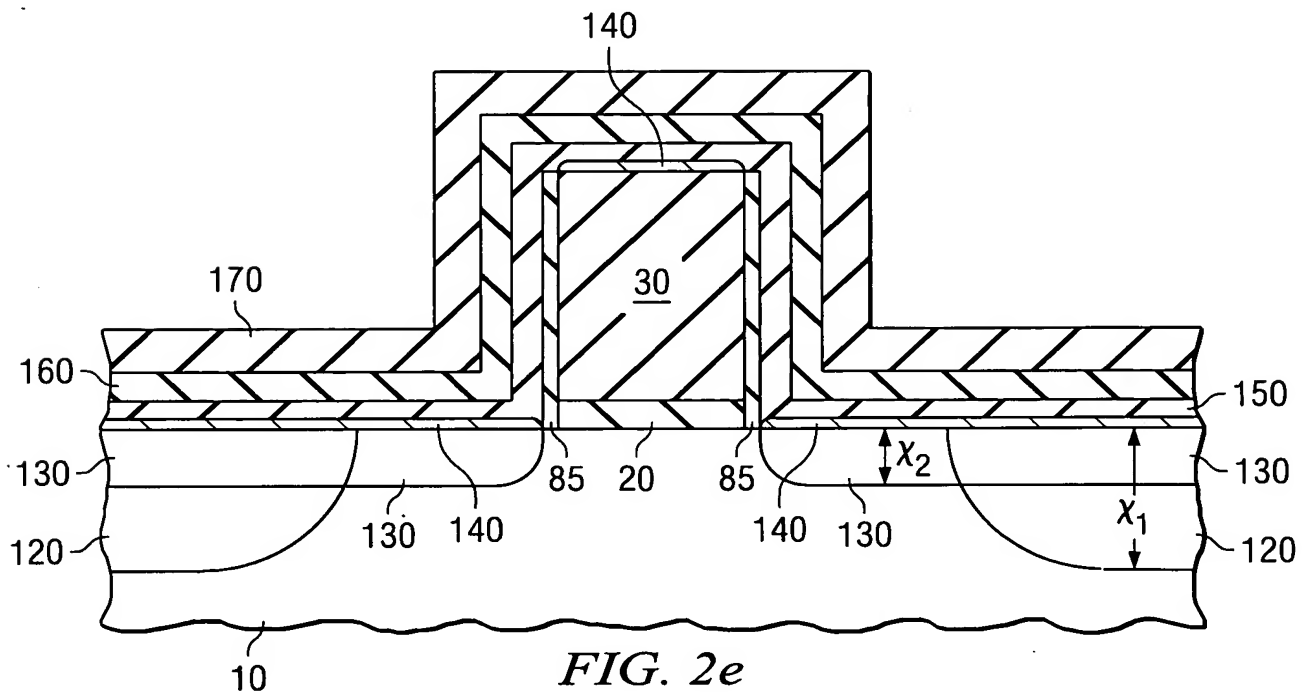
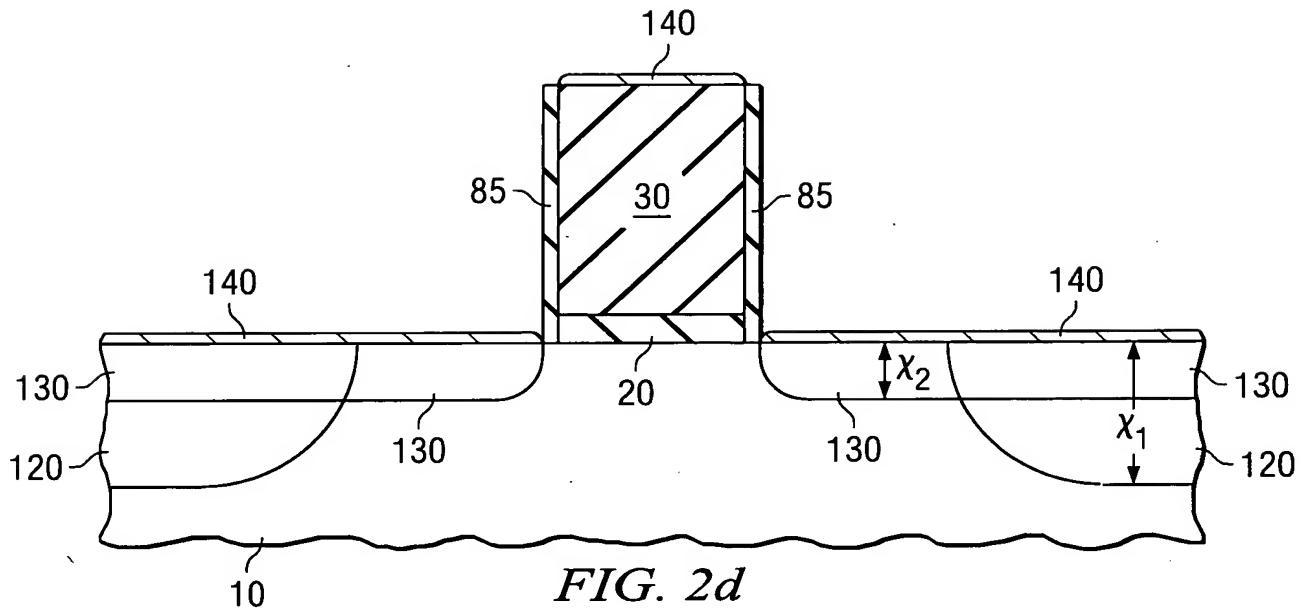
**FIG. 1**  
(PRIOR ART)



**FIG. 2a**



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A detailed cross-sectional diagram of a semiconductor device. At the base is a substrate labeled 10, which contains two horizontal layers: layer 120 at the bottom and layer 130 above it. On top of layer 130, there is a central rectangular region labeled 30, which is filled with diagonal hatching. This central region is flanked by two semi-circular regions labeled 210, also filled with diagonal hatching. Vertical lines, each labeled 85, separate the central rectangular region from the semi-circular regions. Below the central region, there is a thin layer labeled 20, and below that, another thin layer labeled 145. To the left and right of the central assembly, there are additional structures consisting of a semi-circular region 210, a thin layer 145, and a top layer 185. Dimensions are indicated by arrows:  $x_1$  is the vertical distance between layers 120 and 130 on the far right;  $x_2$  is the vertical distance between layers 130 and 145 under the central region;  $x_3$  is the vertical distance between layers 145 and 20 under the central region; and  $x_4$  is the vertical distance between layers 130 and 185 on the far right.

